# HB52E648EN-A6B/B6B, HB52E649EN-A6B/B6B

512 MB Unbuffered SDRAM DIMM, 100 MHz Memory Bus
(HB52E648EN) 64-Mword × 64-bit, 2-Bank Module
(16 pcs of 32 M × 8 Components)
(HB52E649EN) 64-Mword × 72-bit, 2-Bank Module
(18 pcs of 32 M × 8 Components)
PC100 SDRAM

HITACHI

ADE-203-1116A (Z)
Preliminary
Rev. 0.1
Nov. 29, 1999

## Description

The HB52E648EN, HB52E649EN belong to 8-byte DIMM (Dual In-line Memory Module) family, and have been developed as an optimized main memory solution for 8-byte processor applications. They are synchronous Dynamic RAM Module, mounted 256-Mbit SDRAMs (HM5225805BTT) sealed in TSOP package, and 1 piece of serial EEPROM (2-kbit EEPROM) for Presence Detect (PD). The HB52E648EN is organized 32M × 64 × 2-bank mounted 16 pieces of 256-Mbit SDRAM. The HB52E649EN is organized 32M × 72 × 2-bank mounted 18 pieces of 256-Mbit SDRAM. An outline of the products is 168-pin socket type package (dual lead out). Therefore, they make high density mounting possible without surface mount technology. They provide common data inputs and outputs. Decoupling capacitors are mounted beside each TSOP on the module board.

## Features

- Fully compatible with : JEDEC standard outline 8-byte DIMM
  : Intel PCB Reference design (Rev. 1.0)
- 168-pin socket type package (dual lead out)
  — Outline: 133.37 mm (Length) × 34.925 mm (Height) × 4.00 mm (Thickness)
  — Lead pitch: 1.27 mm
- 3.3 V power supply
- Clock frequency: 100 MHz (max)
- LVTTL interface

Preliminary: The specification of this device are subject to change without notice. Please contact your nearest Hitachi's Sales Dept. regarding specification.

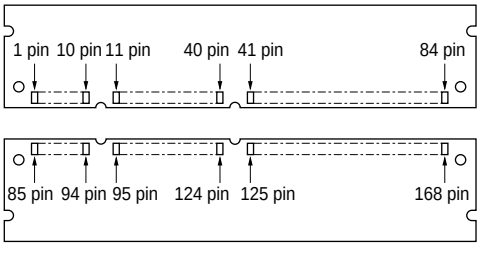
Hitachi semiconductor

- Data bus width : × 64 Non parity (HB52E648EN)
  : × 72 ECC (HB52E649EN)
- Single pulsed $\overline{RAS}$
- 4 Banks can operates simultaneously and independently
- Burst read/write operation and burst read/single write operation capability
- Programmable burst length: 1/2/4/8
- 2 variations of burst sequence
  — Sequential
  — Interleave
- Programmable $\overline{CE}$ latency : 2/3 (HB52E648EN/52E649EN-A6B)
  : 3 (HB52E648EN/52E649EN-B6B)
- Byte control by DQMB
- Refresh cycles: 8192 refresh cycles/64 ms
- 2 variations of refresh
  — Auto refresh
  — Self refresh

## Ordering Information

| Type No. | Frequency | $\overline{CE}$ latency | Package | Contact pad |
|---|---|---|---|---|
| HB52E648EN-A6B | 100 MHz | 2/3 | 168-pin dual lead out socket type | Gold |
| HB52E648EN-B6B | 100 MHz | 3 | | |
| HB52E649EN-A6B | 100 MHz | 2/3 | | |
| HB52E649EN-B6B | 100 MHz | 3 | | |

## Pin Arrangement



(HB52E648EN)

| Pin No. | Pin name | Pin No. | Pin name | Pin No. | Pin name | Pin No. | Pin name |
|---|---|---|---|---|---|---|---|
| 1 | $V_{SS}$ | 43 | $V_{SS}$ | 85 | $V_{SS}$ | 127 | $V_{SS}$ |
| 2 | DQ0 | 44 | NC | 86 | DQ32 | 128 | CKE0 |
| 3 | DQ1 | 45 | $\overline{S2}$ | 87 | DQ33 | 129 | NC ($\overline{S3}$)*2 |
| 4 | DQ2 | 46 | DQMB2 | 88 | DQ34 | 130 | DQMB6 |
| 5 | DQ3 | 47 | DQMB3 | 89 | DQ35 | 131 | DQMB7 |
| 6 | $V_{CC}$ | 48 | NC | 90 | $V_{CC}$ | 132 | NC |
| 7 | DQ4 | 49 | $V_{CC}$ | 91 | DQ36 | 133 | $V_{CC}$ |
| 8 | DQ5 | 50 | NC | 92 | DQ37 | 134 | NC |
| 9 | DQ6 | 51 | NC | 93 | DQ38 | 135 | NC |
| 10 | DQ7 | 52 | NC | 94 | DQ39 | 136 | NC |
| 11 | DQ8 | 53 | NC | 95 | DQ40 | 137 | NC |
| 12 | $V_{SS}$ | 54 | $V_{SS}$ | 96 | $V_{SS}$ | 138 | $V_{SS}$ |
| 13 | DQ9 | 55 | DQ16 | 97 | DQ41 | 139 | DQ48 |
| 14 | DQ10 | 56 | DQ17 | 98 | DQ42 | 140 | DQ49 |
| 15 | DQ11 | 57 | DQ18 | 99 | DQ43 | 141 | DQ50 |
| 16 | DQ12 | 58 | DQ19 | 100 | DQ44 | 142 | DQ51 |
| 17 | DQ13 | 59 | $V_{CC}$ | 101 | DQ45 | 143 | $V_{CC}$ |
| 18 | $V_{CC}$ | 60 | DQ20 | 102 | $V_{CC}$ | 144 | DQ52 |
| 19 | DQ14 | 61 | NC | 103 | DQ46 | 145 | NC |
| 20 | DQ15 | 62 | NC | 104 | DQ47 | 146 | NC |
| 21 | NC | 63 | NC (CKE1)*1 | 105 | NC | 147 | NC |
| 22 | NC | 64 | $V_{SS}$ | 106 | NC | 148 | $V_{SS}$ |
| 23 | $V_{SS}$ | 65 | DQ21 | 107 | $V_{SS}$ | 149 | DQ53 |
| 24 | NC | 66 | DQ22 | 108 | NC | 150 | DQ54 |
| 25 | NC | 67 | DQ23 | 109 | NC | 151 | DQ55 |

| Pin No. | Pin name | Pin No. | Pin name | Pin No. | Pin name | Pin No. | Pin name |
|---|---|---|---|---|---|---|---|
| 26 | $V_{CC}$ | 68 | $V_{SS}$ | 110 | $V_{CC}$ | 152 | $V_{SS}$ |
| 27 | $\overline{W}$ | 69 | DQ24 | 111 | $\overline{CE}$ | 153 | DQ56 |
| 28 | DQMB0 | 70 | DQ25 | 112 | DQMB4 | 154 | DQ57 |
| 29 | DQMB1 | 71 | DQ26 | 113 | DQMB5 | 155 | DQ58 |
| 30 | $\overline{S0}$ | 72 | DQ27 | 114 | NC ($\overline{S1}$)*[3] | 156 | DQ59 |
| 31 | NC | 73 | $V_{CC}$ | 115 | $\overline{RE}$ | 157 | $V_{CC}$ |
| 32 | $V_{SS}$ | 74 | DQ28 | 116 | $V_{SS}$ | 158 | DQ60 |
| 33 | A0 | 75 | DQ29 | 117 | A1 | 159 | DQ61 |
| 34 | A2 | 76 | DQ30 | 118 | A3 | 160 | DQ62 |
| 35 | A4 | 77 | DQ31 | 119 | A5 | 161 | DQ63 |
| 36 | A6 | 78 | $V_{SS}$ | 120 | A7 | 162 | $V_{SS}$ |
| 37 | A8 | 79 | CK2 | 121 | A9 | 163 | CK3 |
| 38 | A10 (AP) | 80 | NC | 122 | BA0 | 164 | NC |
| 39 | BA1 | 81 | WP | 123 | A11 | 165 | SA0 |
| 40 | $V_{CC}$ | 82 | SDA | 124 | $V_{CC}$ | 166 | SA1 |
| 41 | $V_{CC}$ | 83 | SCL | 125 | CK1 | 167 | SA2 |
| 42 | CK0 | 84 | $V_{CC}$ | 126 | A12 | 168 | $V_{CC}$ |

Notes: 1. CKE1: HB52E648EN
2. $\overline{S3}$: HB52E648EN
3. $\overline{S1}$: HB52E648EN

(HB52E649EN)

| Pin No. | Pin name | Pin No. | Pin name | Pin No. | Pin name | Pin No. | Pin name |
|---|---|---|---|---|---|---|---|
| 1 | $V_{SS}$ | 43 | $V_{SS}$ | 85 | $V_{SS}$ | 127 | $V_{SS}$ |
| 2 | DQ0 | 44 | NC | 86 | DQ32 | 128 | CKE0 |
| 3 | DQ1 | 45 | $\overline{S2}$ | 87 | DQ33 | 129 | NC ($\overline{S3}$)*2 |
| 4 | DQ2 | 46 | DQMB2 | 88 | DQ34 | 130 | DQMB6 |
| 5 | DQ3 | 47 | DQMB3 | 89 | DQ35 | 131 | DQMB7 |
| 6 | $V_{CC}$ | 48 | NC | 90 | $V_{CC}$ | 132 | NC |
| 7 | DQ4 | 49 | $V_{CC}$ | 91 | DQ36 | 133 | $V_{CC}$ |
| 8 | DQ5 | 50 | NC | 92 | DQ37 | 134 | NC |
| 9 | DQ6 | 51 | NC | 93 | DQ38 | 135 | NC |
| 10 | DQ7 | 52 | CB2 | 94 | DQ39 | 136 | CB6 |
| 11 | DQ8 | 53 | CB3 | 95 | DQ40 | 137 | CB7 |
| 12 | $V_{SS}$ | 54 | $V_{SS}$ | 96 | $V_{SS}$ | 138 | $V_{SS}$ |
| 13 | DQ9 | 55 | DQ16 | 97 | DQ41 | 139 | DQ48 |
| 14 | DQ10 | 56 | DQ17 | 98 | DQ42 | 140 | DQ49 |
| 15 | DQ11 | 57 | DQ18 | 99 | DQ43 | 141 | DQ50 |
| 16 | DQ12 | 58 | DQ19 | 100 | DQ44 | 142 | DQ51 |
| 17 | DQ13 | 59 | $V_{CC}$ | 101 | DQ45 | 143 | $V_{CC}$ |
| 18 | $V_{CC}$ | 60 | DQ20 | 102 | $V_{CC}$ | 144 | DQ52 |
| 19 | DQ14 | 61 | NC | 103 | DQ46 | 145 | NC |
| 20 | DQ15 | 62 | NC | 104 | DQ47 | 146 | NC |
| 21 | CB0 | 63 | NC (CKE1)*1 | 105 | CB4 | 147 | NC |
| 22 | CB1 | 64 | $V_{SS}$ | 106 | CB5 | 148 | $V_{SS}$ |
| 23 | $V_{SS}$ | 65 | DQ21 | 107 | $V_{SS}$ | 149 | DQ53 |
| 24 | NC | 66 | DQ22 | 108 | NC | 150 | DQ54 |
| 25 | NC | 67 | DQ23 | 109 | NC | 151 | DQ55 |
| 26 | $V_{CC}$ | 68 | $V_{SS}$ | 110 | $V_{CC}$ | 152 | $V_{SS}$ |
| 27 | $\overline{W}$ | 69 | DQ24 | 111 | $\overline{CE}$ | 153 | DQ56 |
| 28 | DQMB0 | 70 | DQ25 | 112 | DQMB4 | 154 | DQ57 |
| 29 | DQMB1 | 71 | DQ26 | 113 | DQMB5 | 155 | DQ58 |
| 30 | $\overline{S0}$ | 72 | DQ27 | 114 | NC ($\overline{S1}$)*3 | 156 | DQ59 |
| 31 | NC | 73 | $V_{CC}$ | 115 | $\overline{RE}$ | 157 | $V_{CC}$ |
| 32 | $V_{SS}$ | 74 | DQ28 | 116 | $V_{SS}$ | 158 | DQ60 |
| 33 | A0 | 75 | DQ29 | 117 | A1 | 159 | DQ61 |

| Pin No. | Pin name | Pin No. | Pin name | Pin No. | Pin name | Pin No. | Pin name |
|---|---|---|---|---|---|---|---|
| 34 | A2 | 76 | DQ30 | 118 | A3 | 160 | DQ62 |
| 35 | A4 | 77 | DQ31 | 119 | A5 | 161 | DQ63 |
| 36 | A6 | 78 | $V_{SS}$ | 120 | A7 | 162 | $V_{SS}$ |
| 37 | A8 | 79 | CK2 | 121 | A9 | 163 | CK3 |
| 38 | A10 (AP) | 80 | NC | 122 | BA0 | 164 | NC |
| 39 | BA1 | 81 | WP | 123 | A11 | 165 | SA0 |
| 40 | $V_{CC}$ | 82 | SDA | 124 | $V_{CC}$ | 166 | SA1 |
| 41 | $V_{CC}$ | 83 | SCL | 125 | CK1 | 167 | SA2 |
| 42 | CK0 | 84 | $V_{CC}$ | 126 | A12 | 168 | $V_{CC}$ |

Notes: 1. CKE1: HB52E649EN
2. $\overline{S3}$: HB52E649EN
3. $\overline{S1}$: HB52E649EN

## Pin Description (HB52E648EN)

| Pin name | Function |
|---|---|
| A0 to A12 | Address input<br>— Row address A0 to A12<br>— Column address A0 to A9 |
| BA0/BA1 | Bank select address |
| DQ0 to DQ63 | Data input/output |
| $\overline{S0}$ to $\overline{S3}$ | Chip select input |
| $\overline{RE}$ | Row enable (RAS) input |
| $\overline{CE}$ | Column enable (CAS) input |
| $\overline{W}$ | Write enable input |
| DQMB0 to DQMB7 | Byte data mask |
| CK0 to CK3 | Clock input |
| CKE0, CKE1 | Clock enable input |
| WP | Write protect for serial PD |
| SDA | Data input/output for serial PD |
| SCL | Clock input for serial PD |
| SA0 to SA2 | Serial address input |
| $V_{CC}$ | Primary positive power supply |
| $V_{SS}$ | Ground |
| NC | No connection |

## Pin Description (HB52E649EN)

| Pin name | Function |
|---|---|
| A0 to A12 | Address input<br>— Row address A0 to A12<br>— Column address A0 to A9 |
| BA0/BA1 | Bank select address |
| DQ0 to DQ63 | Data input/output |
| CB0 to CB7 | Check bit (Data input/output) |
| $\overline{S0}$ to $\overline{S3}$ | Chip select input |
| $\overline{RE}$ | Row enable (RAS) input |
| $\overline{CE}$ | Column enable (CAS) input |
| $\overline{W}$ | Write enable input |
| DQMB0 to DQMB7 | Byte data mask |
| CK0 to CK3 | Clock input |
| CKE0, CKE1 | Clock enable input |
| WP | Write protect for serial PD |
| SDA | Data input/output for serial PD |
| SCL | Clock input for serial PD |
| SA0 to SA2 | Serial address input |
| $V_{CC}$ | Primary positive power supply |
| $V_{SS}$ | Ground |
| NC | No connection |

## Serial PD Matrix*[1]

| Byte No. | Function described | Bit7 | Bit6 | Bit5 | Bit4 | Bit3 | Bit2 | Bit1 | Bit0 | Hex value | Comments |
|---|---|---|---|---|---|---|---|---|---|---|---|
| 0 | Number of bytes used by module manufacturer | 1 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 80 | 128 |
| 1 | Total SPD memory size | 0 | 0 | 0 | 0 | 1 | 0 | 0 | 0 | 08 | 256 byte |
| 2 | Memory type | 0 | 0 | 0 | 0 | 0 | 1 | 0 | 0 | 04 | SDRAM |
| 3 | Number of row addresses bits | 0 | 0 | 0 | 0 | 1 | 1 | 0 | 1 | 0D | 13 |
| 4 | Number of column addresses bits | 0 | 0 | 0 | 0 | 1 | 0 | 1 | 0 | 0A | 10 |
| 5 | Number of banks | 0 | 0 | 0 | 0 | 0 | 0 | 1 | 0 | 02 | 2 |
| 6 | Module data width<br>(HB52E648EN) | 0 | 1 | 0 | 0 | 0 | 0 | 0 | 0 | 40 | 64 |
| | (HB52E649EN) | 0 | 1 | 0 | 0 | 1 | 0 | 0 | 0 | 48 | 72 |
| 7 | Module data width (continued) | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 00 | 0 (+) |
| 8 | Module interface signal levels | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 1 | 01 | LVTTL |
| 9 | SDRAM cycle time (highest $\overline{CE}$ latency)<br>10 ns | 1 | 0 | 1 | 0 | 0 | 0 | 0 | 0 | A0 | CL = 3 |
| 10 | SDRAM access from Clock (highest $\overline{CE}$ latency)<br>6 ns | 0 | 1 | 1 | 0 | 0 | 0 | 0 | 0 | 60 | |
| 11 | Module configuration type<br>(HB52E648EN) | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 00 | Non parity |
| | (HB52E649EN) | 0 | 0 | 0 | 0 | 0 | 0 | 1 | 0 | 02 | ECC |
| 12 | Refresh rate/type | 1 | 0 | 0 | 0 | 0 | 0 | 1 | 0 | 82 | Normal (7.8125 µs) Self refresh |
| 13 | SDRAM width | 0 | 0 | 0 | 0 | 1 | 0 | 0 | 0 | 08 | 32M × 8 |
| 14 | Error checking SDRAM width<br>(HB52E648EN) | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 00 | — |
| | (HB52E649EN) | 0 | 0 | 0 | 0 | 1 | 0 | 0 | 0 | 08 | × 8 |
| 15 | SDRAM device attributes: minimum clock delay for back-to-back random column addresses | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 1 | 01 | 1 CLK |
| 16 | SDRAM device attributes: Burst lengths supported | 0 | 0 | 0 | 0 | 1 | 1 | 1 | 1 | 0F | 1, 2, 4, 8 |

| Byte No. | Function described | Bit7 | Bit6 | Bit5 | Bit4 | Bit3 | Bit2 | Bit1 | Bit0 | Hex value | Comments |
|---|---|---|---|---|---|---|---|---|---|---|---|
| 17 | SDRAM device attributes: number of banks on SDRAM device | 0 | 0 | 0 | 0 | 0 | 1 | 0 | 0 | 04 | 4 |
| 18 | SDRAM device attributes: $\overline{CE}$ latency | 0 | 0 | 0 | 0 | 0 | 1 | 1 | 0 | 06 | 2, 3 |
| 19 | SDRAM device attributes: $\overline{S}$ latency | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 1 | 01 | 0 |
| 20 | SDRAM device attributes: $\overline{W}$ latency | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 1 | 01 | 0 |
| 21 | SDRAM module attributes | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 00 | Non buffer |
| 22 | SDRAM device attributes: General | 0 | 0 | 0 | 0 | 1 | 1 | 1 | 0 | 0E | $V_{CC} \pm 10\%$ |
| 23 | SDRAM cycle time (2nd highest $\overline{CE}$ latency) (-A6B) 10 ns | 1 | 0 | 1 | 0 | 0 | 0 | 0 | 0 | A0 | CL = 2 |
| | SDRAM cycle time (2nd highest $\overline{CE}$ latency) (-B6B) 15 ns | 1 | 1 | 1 | 1 | 0 | 0 | 0 | 0 | F0 | |
| 24 | SDRAM access from Clock (2nd highest $\overline{CE}$ latency) (-A6B) 6 ns | 0 | 1 | 1 | 0 | 0 | 0 | 0 | 0 | 60 | CL = 2 |
| | SDRAM access from Clock (2nd highest $\overline{CE}$ latency) (-B6B) 9 ns | 1 | 0 | 0 | 1 | 0 | 0 | 0 | 0 | 90 | |
| 25 | SDRAM cycle time (3rd highest $\overline{CE}$ latency) Undefined | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 00 | |
| 26 | SDRAM access from Clock (3rd highest $\overline{CE}$ latency) Undefined | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 00 | |
| 27 | Minimum row precharge time | 0 | 0 | 0 | 1 | 0 | 1 | 0 | 0 | 14 | 20 ns |
| 28 | Row active to row active min | 0 | 0 | 0 | 1 | 0 | 1 | 0 | 0 | 14 | 20 ns |
| 29 | $\overline{RE}$ to $\overline{CE}$ delay min | 0 | 0 | 0 | 1 | 0 | 1 | 0 | 0 | 14 | 20 ns |
| 30 | Minimum $\overline{RE}$ pulse width | 0 | 0 | 1 | 1 | 0 | 0 | 1 | 0 | 32 | 50 ns |
| 31 | Density of each bank on module | 0 | 1 | 0 | 0 | 0 | 0 | 0 | 0 | 40 | 2 bank 256 M byte |
| 32 | Address and command signal input setup time | 0 | 0 | 1 | 0 | 0 | 0 | 0 | 0 | 20 | 2.0 ns |
| 33 | Address and command signal input hold time | 0 | 0 | 0 | 1 | 0 | 0 | 0 | 0 | 10 | 1.0 ns |
| 34 | Data signal input setup time | 0 | 0 | 1 | 0 | 0 | 0 | 0 | 0 | 20 | 2.0 ns |

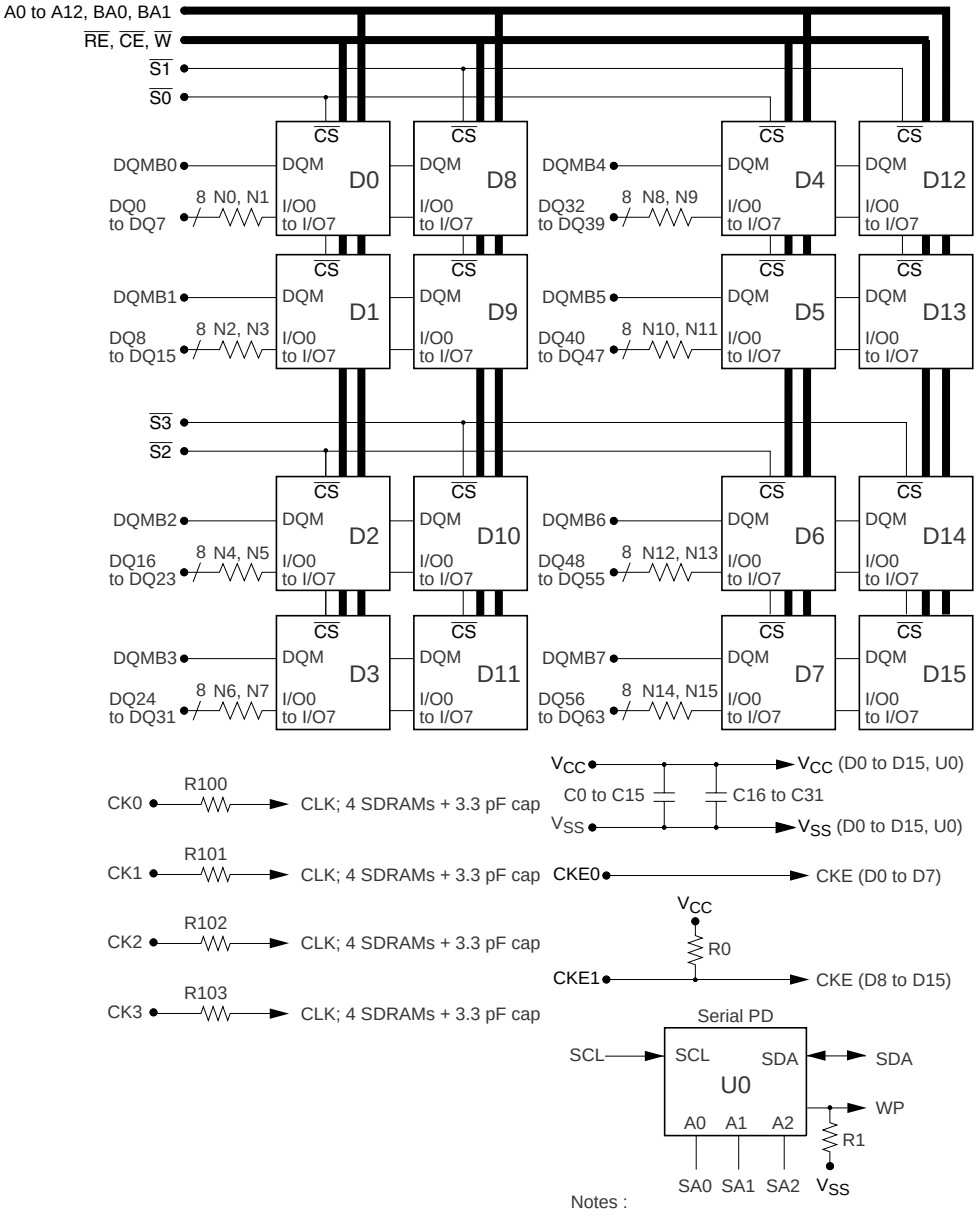
| Byte No. | Function described | Bit7 | Bit6 | Bit5 | Bit4 | Bit3 | Bit2 | Bit1 | Bit0 | Hex value | Comments |
|---|---|---|---|---|---|---|---|---|---|---|---|
| 35 | Data signal input hold time | 0 | 0 | 0 | 1 | 0 | 0 | 0 | 0 | 10 | 1.0 ns |
| 36 to 61 | Superset information | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 00 | Future use |
| 62 | SPD data revision code | 0 | 0 | 0 | 1 | 0 | 0 | 1 | 0 | 12 | Rev.1.2A |
| 63 | Checksum for bytes 0 to 62 (HB52E648EN-A6B) | 1 | 0 | 1 | 1 | 1 | 0 | 1 | 0 | BA | 186 |
| | (HB52E648EN-B6B) | 0 | 0 | 1 | 1 | 1 | 0 | 1 | 0 | 3A | 58 |
| | (HB52E649EN-A6B) | 1 | 1 | 0 | 0 | 1 | 1 | 0 | 0 | CC | 204 |
| | (HB52E649EN-B6B) | 0 | 1 | 0 | 0 | 1 | 1 | 0 | 0 | 4C | 76 |
| 64 | Manufacturer's JEDEC ID code | 0 | 0 | 0 | 0 | 0 | 1 | 1 | 1 | 07 | HITACHI |
| 65 to 71 | Manufacturer's JEDEC ID code | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 00 | |
| 72 | Manufacturing location | × | × | × | × | × | × | × | × | ×× | *[3] (ASCII-8bit code) |
| 73 | Manufacturer's part number | 0 | 1 | 0 | 0 | 1 | 0 | 0 | 0 | 48 | H |
| 74 | Manufacturer's part number | 0 | 1 | 0 | 0 | 0 | 0 | 1 | 0 | 42 | B |
| 75 | Manufacturer's part number | 0 | 0 | 1 | 1 | 0 | 1 | 0 | 1 | 35 | 5 |
| 76 | Manufacturer's part number | 0 | 0 | 1 | 1 | 0 | 0 | 1 | 0 | 32 | 2 |
| 77 | Manufacturer's part number | 0 | 1 | 0 | 0 | 0 | 1 | 0 | 1 | 45 | E |
| 78 | Manufacturer's part number | 0 | 0 | 1 | 1 | 0 | 1 | 1 | 0 | 36 | 6 |
| 79 | Manufacturer's part number | 0 | 0 | 1 | 1 | 0 | 1 | 0 | 0 | 34 | 4 |
| 80 | Manufacturer's part number (HB52E648EN) | 0 | 0 | 1 | 1 | 1 | 0 | 0 | 0 | 38 | 8 |
| | (HB52E649EN) | 0 | 0 | 1 | 1 | 1 | 0 | 0 | 1 | 39 | 9 |
| 81 | Manufacturer's part number | 0 | 1 | 0 | 0 | 0 | 1 | 0 | 1 | 45 | E |
| 82 | Manufacturer's part number | 0 | 1 | 0 | 0 | 1 | 1 | 1 | 0 | 4E | N |
| 83 | Manufacturer's part number | 0 | 0 | 1 | 0 | 1 | 1 | 0 | 1 | 2D | — |
| 84 | Manufacturer's part number (HB52E648EN/649EN-A6B) | 0 | 1 | 0 | 0 | 0 | 0 | 0 | 1 | 41 | A |
| | (HB52E648EN/649EN-B6B) | 0 | 1 | 0 | 0 | 0 | 0 | 1 | 0 | 42 | B |
| 85 | Manufacturer's part number | 0 | 0 | 1 | 1 | 0 | 1 | 1 | 0 | 36 | 6 |
| 86 | Manufacturer's part number | 0 | 1 | 0 | 0 | 0 | 0 | 1 | 0 | 42 | B |
| 87 | Manufacturer's part number | 0 | 0 | 1 | 0 | 0 | 0 | 0 | 0 | 20 | (Space) |
| 88 | Manufacturer's part number | 0 | 0 | 1 | 0 | 0 | 0 | 0 | 0 | 20 | (Space) |

| Byte No. | Function described | Bit7 | Bit6 | Bit5 | Bit4 | Bit3 | Bit2 | Bit1 | Bit0 | Hex value | Comments |
|---|---|---|---|---|---|---|---|---|---|---|---|
| 89 | Manufacturer's part number | 0 | 0 | 1 | 0 | 0 | 0 | 0 | 0 | 20 | (Space) |
| 90 | Manufacturer's part number | 0 | 0 | 1 | 0 | 0 | 0 | 0 | 0 | 20 | (Space) |
| 91 | Revision code | 0 | 0 | 1 | 1 | 0 | 0 | 0 | 0 | 30 | Initial |
| 92 | Revision code | 0 | 0 | 1 | 0 | 0 | 0 | 0 | 0 | 20 | (Space) |
| 93 | Manufacturing date | × | × | × | × | × | × | × | × | ×× | Year code (BCD)*4 |
| 94 | Manufacturing date | × | × | × | × | × | × | × | × | ×× | Week code (BCD)*4 |
| 95 to 98 | Assembly serial number | *6 | | | | | | | | | |
| 99 to 125 | Manufacturer specific data | — | — | — | — | — | — | — | — | — | *5 |
| 126 | Intel specification frequency | 0 | 1 | 1 | 0 | 0 | 1 | 0 | 0 | 64 | 100 MHz |
| 127 | Intel specification $\overline{CE}$# latency support | | | | | | | | | | |
| | (HB52E648EN/649EN-A6B) | 1 | 1 | 1 | 1 | 1 | 1 | 1 | 1 | FF | CL = 2, 3 |
| | (HB52E648EN/649EN-B6B) | 1 | 1 | 1 | 1 | 1 | 1 | 0 | 1 | FD | CL = 3 |

Notes: 1. All serial PD data are not protected. 0: Serial data, "driven Low", 1: Serial data, "driven High" These SPD are based on Intel specification (Rev.1.2A).

2. Regarding byte32 to 35, based on JEDEC Committee Ballot JC42.5-97-119.
3. Byte72 is manufacturing location code. (ex: In case of Japan, byte72 is 4AH. 4AH shows "J" on ASCII code.)
4. Regarding byte93 and 94, based on JEDEC Committee Ballot JC42.5-97-135. BCD is "Binary Coded Decimal".
5. All bits of 99 through 125 are not defined ("1" or "0").
6. Bytes 95 through 98 are assembly serial number.

## Block Diagram (HB52E648EN)

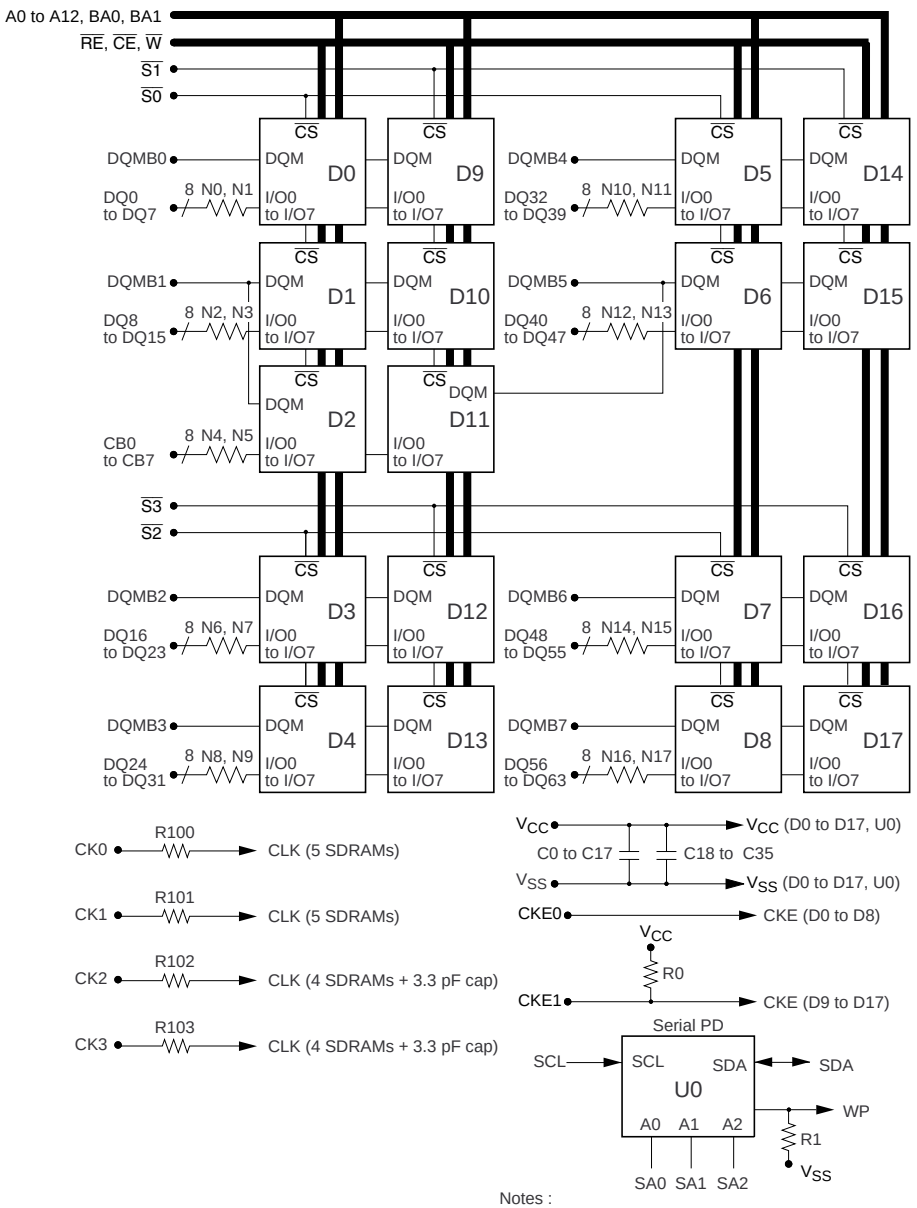



Notes :

1. The SDA pull-up resistor is required due to the open-drain/open-collector output.
2. The SCL pull-up resistor is recommended because of the normal SCL line inacitve "high" state.

* D0 to D15: HM5225805
U0: 2-kbit EEPROM
C0 to C15: 0.33 µF, C16 to C31: 0.10 µF
R0: 10 kΩ, R1: 47 kΩ
N0 to N15: Network registor 10 Ω
R100 to R103: 10 Ω

## Block Diagram (HB52E649EN)




Notes :

1. The SDA pull-up resistor is required due to the open-drain/open-collector output.
2. The SCL pull-up resistor is recommended because of the normal SCL line inacitve "high" state.
3. SDRAM D11 DQMB input is wired to DQMB5

* D0 to D17: HM5225805
U0: 2-kbit EEPROM
C0 to C17: 0.33 µF, C18 to C35: 0.10 µF
R0: 10 kΩ, R1: 47 kΩ
N0 to N17: Network registor 10 Ω
R100 to R103: 10 Ω

## Absolute Maximum Ratings

| Parameter | Symbol | Value | Unit | Note |
|---|---|---|---|---|
| Voltage on any pin relative to $V_{SS}$ | $V_T$ | –0.5 to $V_{CC}$ + 0.5 (≤ 4.6 (max)) | V | 1 |
| Supply voltage relative to $V_{SS}$ | $V_{CC}$ | –0.5 to +4.6 | V | 1 |
| Short circuit output current | Iout | 50 | mA | |
| Power dissipation (HB52E648EN) | $P_T$ | 8.0 | W | |
| Power dissipation (HB52E649EN) | $P_T$ | 9.0 | W | |
| Operating temperature | Topr | 0 to +65 | °C | |
| Storage temperature | Tstg | –55 to +125 | °C | |

Note: 1. Respect to $V_{SS}$

## DC Operating Conditions (Ta = 0 to +65°C)

| Parameter | Symbol | Min | Max | Unit | Notes |
|---|---|---|---|---|---|
| Supply voltage | $V_{CC}$ | 3.0 | 3.6 | V | 1, 2 |
| | $V_{SS}$ | 0 | 0 | V | 3 |
| Input high voltage | $V_{IH}$ | 2.0 | $V_{CC}$ + 0.3 | V | 1, 4 |
| Input low voltage | $V_{IL}$ | –0.3 | 0.8 | V | 1, 5 |

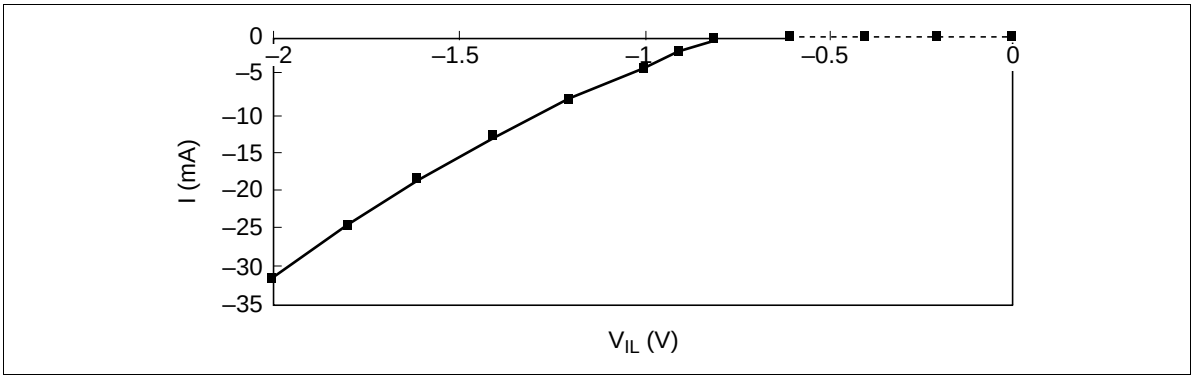
Notes: 1. All voltage referred to $V_{SS}$
2. The supply voltage with all $V_{CC}$ pins must be on the same level.
3. The supply voltage with all $V_{SS}$ pins must be on the same level.
4. $V_{IH}$ (max) = $V_{CC}$ + 2.0 V for pulse with ≤ 3 ns at $V_{CC}$.
5. $V_{IL}$ (min) = $V_{SS}$ – 2.0 V for pulse width ≤ 3 ns at $V_{SS}$.

## $V_{IL}/V_{IH}$ Clamp (Component characteristic)

This SDRAM component has $V_{IL}$ and $V_{IH}$ clamp for CK, CKE, $\overline{S}$, DQMB and DQ pins.

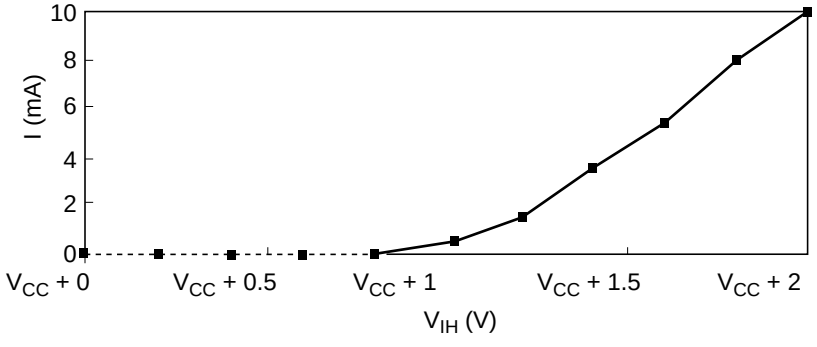
### Minimum $V_{IL}$ Clamp Current

| $V_{IL}$ (V) | I (mA) |
|---|---|
| –2 | –32 |
| –1.8 | –25 |
| –1.6 | –19 |
| –1.4 | –13 |
| –1.2 | –8 |
| –1 | –4 |
| –0.9 | –2 |
| –0.8 | –0.6 |
| –0.6 | 0 |
| –0.4 | 0 |
| –0.2 | 0 |
| 0 | 0 |



**Minimum $V_{IH}$ Clamp Current**

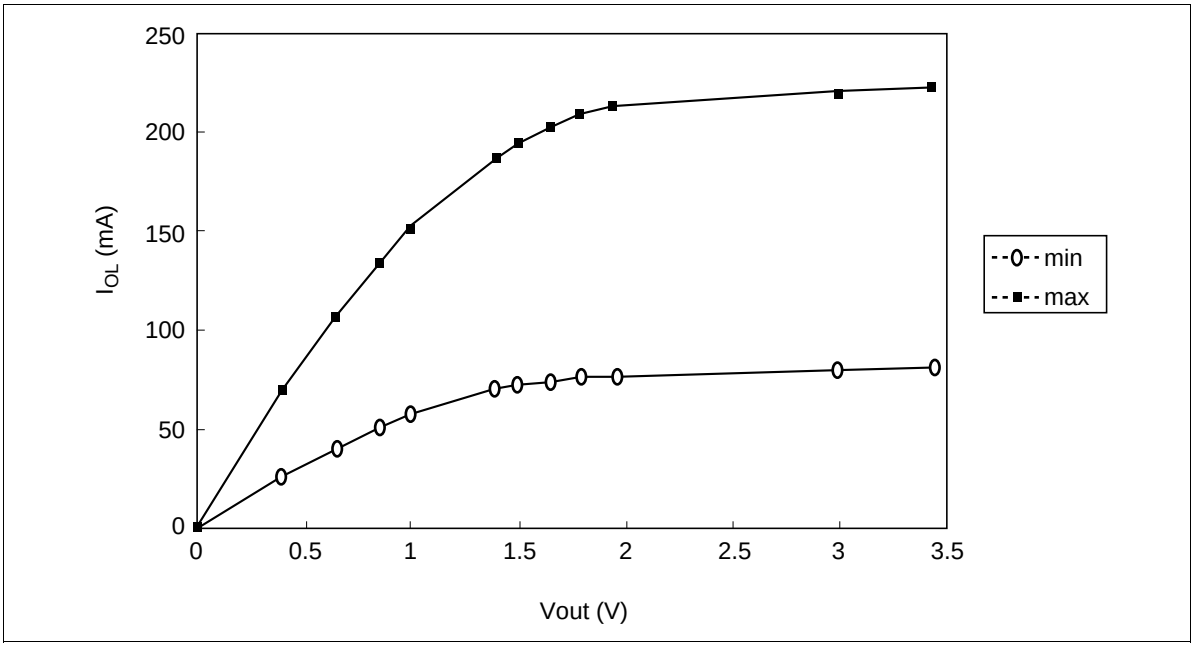
| $V_{IH}$ (V) | I (mA) |
|---|---|
| $V_{CC}$ + 2 | 10 |
| $V_{CC}$ + 1.8 | 8 |
| $V_{CC}$ + 1.6 | 5.5 |
| $V_{CC}$ + 1.4 | 3.5 |
| $V_{CC}$ + 1.2 | 1.5 |
| $V_{CC}$ + 1 | 0.3 |
| $V_{CC}$ + 0.8 | 0 |
| $V_{CC}$ + 0.6 | 0 |
| $V_{CC}$ + 0.4 | 0 |
| $V_{CC}$ + 0.2 | 0 |
| $V_{CC}$ + 0 | 0 |



## $I_{OL}/I_{OH}$ Characteristics (Component characteristic)

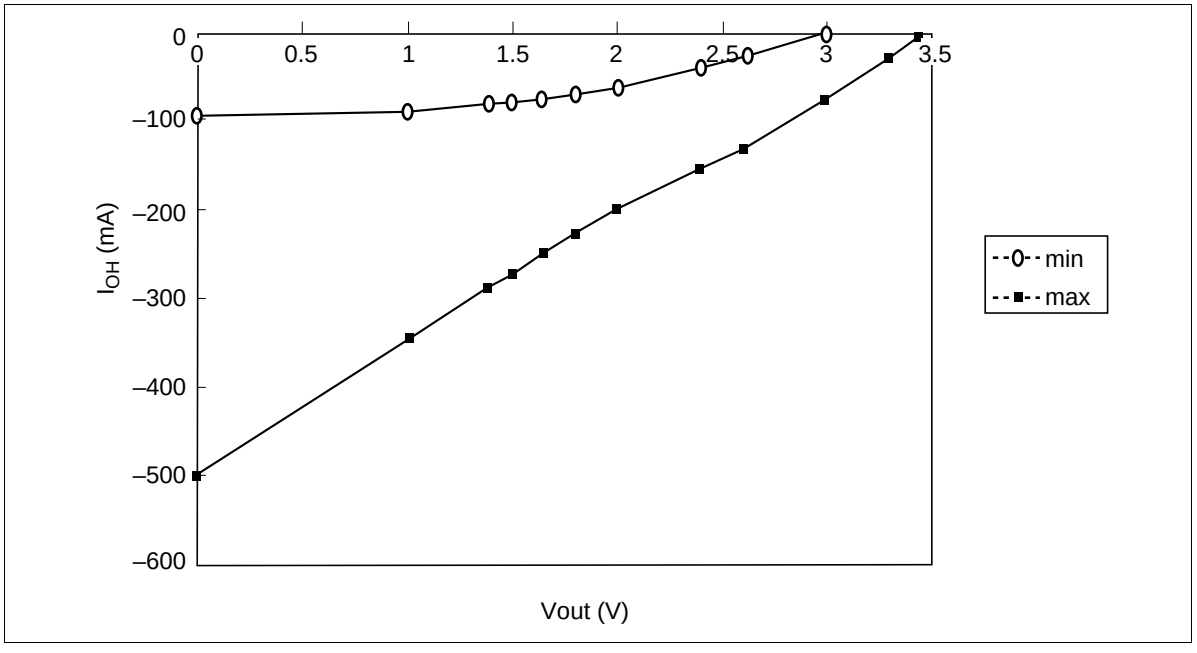
**Output Low Current** ($I_{OL}$)

| | $I_{OL}$ | $I_{OL}$ |
|---|---|---|
| **Vout (V)** | **Min (mA)** | **Max (mA)** |
| 0 | 0 | 0 |
| 0.4 | 27 | 71 |
| 0.65 | 41 | 108 |
| 0.85 | 51 | 134 |
| 1 | 58 | 151 |
| 1.4 | 70 | 188 |
| 1.5 | 72 | 194 |
| 1.65 | 75 | 203 |
| 1.8 | 77 | 209 |
| 1.95 | 77 | 212 |
| 3 | 80 | 220 |
| 3.45 | 81 | 223 |



**Output High Current** ($I_{OH}$) (Ta = 0 to 65˚C, $V_{CC}$ = 3.0 V to 3.45 V, $V_{SS}$ = 0 V)

| | $I_{OH}$ | $I_{OH}$ |
|---|---|---|
| **Vout (V)** | **Min (mA)** | **Max (mA)** |
| 3.45 | — | –3 |
| 3.3 | — | –28 |
| 3 | 0 | –75 |
| 2.6 | –21 | –130 |
| 2.4 | –34 | –154 |
| 2 | –59 | –197 |
| 1.8 | –67 | –227 |
| 1.65 | –73 | –248 |
| 1.5 | –78 | –270 |
| 1.4 | –81 | –285 |
| 1 | –89 | –345 |
| 0 | –93 | –503 |



**DC Characteristics** (Ta = 0 to 65°C, $V_{CC}$ = 3.3 V ± 0.3 V, $V_{SS}$ = 0 V) (HB52E648EN)

| | | HB52E648EN -A6B/B6B | | | | |
|---|---|---|---|---|---|---|
| **Parameter** | **Symbol** | **Min** | **Max** | **Unit** | **Test conditions** | **Notes** |
| Operating current ($\overline{CE}$ latency = 2) | $I_{CC1}$ | — | 1000 | mA | Burst length = 1<br>$t_{RC}$ = min | 1, 2, 3 |
| ($\overline{CE}$ latency = 3) | $I_{CC1}$ | — | 1000 | mA | | |
| Standby current in power down | $I_{CC2P}$ | — | 48 | mA | CKE = $V_{IL}$, $t_{CK}$ = 12 ns | 6 |
| Standby current in power down (input signal stable) | $I_{CC2PS}$ | — | 32 | mA | CKE = $V_{IL}$, $t_{CK}$ = ∞ | 7 |
| Standby current in non power down | $I_{CC2N}$ | — | 320 | mA | CKE, $\overline{S}$ = $V_{IH}$,<br>$t_{CK}$ = 12 ns | 4 |
| Active standby current in power down | $I_{CC3P}$ | — | 64 | mA | CKE = $V_{IL}$, $t_{CK}$ = 12 ns | 1, 2, 6 |
| Active standby current in non power down | $I_{CC3N}$ | — | 480 | mA | CKE, $\overline{S}$ = $V_{IH}$,<br>$t_{CK}$ = 12 ns | 1, 2, 4 |
| Burst operating current ($\overline{CE}$ latency = 2) | $I_{CC4}$ | — | 1040 | mA | $t_{CK}$ = min, BL = 4 | 1, 2, 5 |
| ($\overline{CE}$ latency = 3) | $I_{CC4}$ | — | 1040 | mA | | |
| Refresh current | $I_{CC5}$ | — | 2000 | mA | $t_{RC}$ = min | 3 |
| Self refresh current | $I_{CC6}$ | — | 48 | mA | $V_{IH} \geq V_{CC}$ – 0.2 V<br>$V_{IL} \leq$ 0.2 V | 8 |
| Input leakage current | $I_{LI}$ | –10 | 10 | µA | 0 ≤ Vin ≤ $V_{CC}$ | |
| Output leakage current | $I_{LO}$ | –10 | 10 | µA | 0 ≤ Vout ≤ $V_{CC}$<br>DQ = disable | |
| Output high voltage | $V_{OH}$ | 2.4 | — | V | $I_{OH}$ = –4 mA | |
| Output low voltage | $V_{OL}$ | — | 0.4 | V | $I_{OL}$ = 4 mA | |

Notes: 1. $I_{CC}$ depends on output load condition when the device is selected. $I_{CC}$ (max) is specified at the output open condition.
2. One bank operation.
3. Input signals are changed once per one clock.
4. Input signals are changed once per two clocks.
5. Input signals are changed once per four clocks.
6. After power down mode, CK operating current.
7. After power down mode, no CK operating current.
8. After self refresh mode set, self refresh current.

## DC Characteristics (Ta = 0 to 65°C, $V_{CC}$ = 3.3 V ± 0.3 V, $V_{SS}$ = 0 V) (HB52E649EN)

| | | HB52E649EN -A6B/B6B | | | | |
|---|---|---|---|---|---|---|
| **Parameter** | **Symbol** | **Min** | **Max** | **Unit** | **Test conditions** | **Notes** |
| Operating current ($\overline{CE}$ latency = 2) | $I_{CC1}$ | — | 1125 | mA | Burst length = 1<br>$t_{RC}$ = min | 1, 2, 3 |
| ($\overline{CE}$ latency = 3) | $I_{CC1}$ | — | 1125 | mA | | |
| Standby current in power down | $I_{CC2P}$ | — | 54 | mA | CKE = $V_{IL}$, $t_{CK}$ = 12 ns | 6 |
| Standby current in power down (input signal stable) | $I_{CC2PS}$ | — | 36 | mA | CKE = $V_{IL}$, $t_{CK}$ = ∞ | 7 |
| Standby current in non power down | $I_{CC2N}$ | — | 360 | mA | CKE, $\overline{S}$ = $V_{IH}$,<br>$t_{CK}$ = 12 ns | 4 |
| Active standby current in power down | $I_{CC3P}$ | — | 72 | mA | CKE = $V_{IL}$, $t_{CK}$ = 12 ns | 1, 2, 6 |
| Active standby current in non power down | $I_{CC3N}$ | — | 540 | mA | CKE, $\overline{S}$ = $V_{IH}$,<br>$t_{CK}$ = 12 ns | 1, 2, 4 |
| Burst operating current ($\overline{CE}$ latency = 2) | $I_{CC4}$ | — | 1170 | mA | $t_{CK}$ = min, BL = 4 | 1, 2, 5 |
| ($\overline{CE}$ latency = 3) | $I_{CC4}$ | — | 1170 | mA | | |
| Refresh current | $I_{CC5}$ | — | 2250 | mA | $t_{RC}$ = min | 3 |
| Self refresh current | $I_{CC6}$ | — | 54 | mA | $V_{IH} \geq V_{CC}$ – 0.2 V<br>$V_{IL} \leq$ 0.2 V | 8 |
| Input leakage current | $I_{LI}$ | –10 | 10 | µA | 0 ≤ Vin ≤ $V_{CC}$ | |
| Output leakage current | $I_{LO}$ | –10 | 10 | µA | 0 ≤ Vout ≤ $V_{CC}$<br>DQ = disable | |
| Output high voltage | $V_{OH}$ | 2.4 | — | V | $I_{OH}$ = –4 mA | |
| Output low voltage | $V_{OL}$ | — | 0.4 | V | $I_{OL}$ = 4 mA | |

Notes: 1. $I_{CC}$ depends on output load condition when the device is selected. $I_{CC}$ (max) is specified at the output open condition.
2. One bank operation.
3. Input signals are changed once per one clock.
4. Input signals are changed once per two clocks.
5. Input signals are changed once per four clocks.
6. After power down mode, CK operating current.
7. After power down mode, no CK operating current.
8. After self refresh mode set, self refresh current.

## Capacitance (Ta = 25°C, $V_{CC}$ = 3.3 V ± 0.3 V) (HB52E648EN)

| Parameter | Symbol | Max | Unit | Notes |
|---|---|---|---|---|
| Input capacitance (Address) | $C_{I1}$ | 105 | pF | 1, 2, 4 |
| Input capacitance ($\overline{RE}$, $\overline{CE}$, $\overline{W}$) | $C_{I2}$ | 90 | pF | 1, 2, 4 |
| Input capacitance (CKE) | $C_{I3}$ | 68 | pF | 1, 2, 4 |
| Input capacitance ($\overline{S}$) | $C_{I4}$ | 38 | pF | 1, 2, 4 |
| Input capacitance (CK) | $C_{I5}$ | 50 | pF | 1, 2, 4 |
| Input capacitance (DQMB) | $C_{I6}$ | 23 | pF | 1, 2, 4 |
| Input/Output capacitance (DQ) | $C_{I/O1}$ | 22 | pF | 1, 2, 3, 4 |

Notes: 1. Capacitance measured with Boonton Meter or effective capacitance measuring method.
2. Measurement condition: f = 1 MHz, 1.4 V bias, 200 mV swing.
3. DQMB = $V_{IH}$ to disable Data-out.
4. This parameter is sampled and not 100% tested.

## Capacitance (Ta = 25°C, $V_{CC}$ = 3.3 V ± 0.3 V) (HB52E649EN)

| Parameter | Symbol | Max | Unit | Notes |
|---|---|---|---|---|
| Input capacitance (Address) | $C_{I1}$ | 112 | pF | 1, 2, 4 |
| Input capacitance ($\overline{RE}$, $\overline{CE}$, $\overline{W}$) | $C_{I2}$ | 97 | pF | 1, 2, 4 |
| Input capacitance (CKE) | $C_{I3}$ | 70 | pF | 1, 2, 4 |
| Input capacitance ($\overline{S}$) | $C_{I4}$ | 40 | pF | 1, 2, 4 |
| Input capacitance (CK) | $C_{I5}$ | 50 | pF | 1, 2, 4 |
| Input capacitance (DQMB) | $C_{I6}$ | 27 | pF | 1, 2, 4 |
| Input/Output capacitance (DQ) | $C_{I/O1}$ | 22 | pF | 1, 2, 3, 4 |

Notes: 1. Capacitance measured with Boonton Meter or effective capacitance measuring method.
2. Measurement condition: f = 1 MHz, 1.4 V bias, 200 mV swing.
3. DQMB = $V_{IH}$ to disable Data-out.
4. This parameter is sampled and not 100% tested.

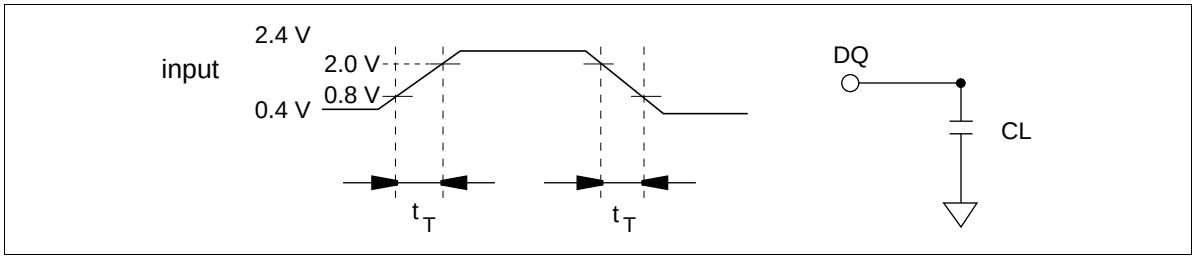
## AC Characteristics (Ta = 0 to 65°C, $V_{CC}$ = 3.3 V ± 0.3 V, $V_{SS}$ = 0 V)

| | | | HB52E648EN/649EN -A6B/B6B | | | |
|---|---|---|---|---|---|---|
| **Parameter** | **HITACHI Symbol** | **PC100 Symbol** | **Min** | **Max** | **Unit** | **Notes** |
| System clock cycle time ($\overline{CE}$ latency = 2) | $t_{CK}$ | Tclk | 10 | — | ns | 1 |
| ($\overline{CE}$ latency = 3) | $t_{CK}$ | Tclk | 10 | — | ns | |
| CK high pulse width | $t_{CKH}$ | Tch | 3 | — | ns | 1 |
| CK low pulse width | $t_{CKL}$ | Tcl | 3 | — | ns | 1 |
| Access time from CK ($\overline{CE}$ latency = 2) | $t_{AC}$ | Tac | — | 6 | ns | 1, 2 |
| ($\overline{CE}$ latency = 3) | $t_{AC}$ | Tac | — | 6 | ns | |
| Data-out hold time | $t_{OH}$ | Toh | 3 | — | ns | 1, 2 |
| CK to Data-out low impedance | $t_{LZ}$ | | 2 | — | ns | 1, 2, 3 |
| CK to Data-out high impedance | $t_{HZ}$ | | — | 6 | ns | 1, 4 |
| Data-in setup time | $t_{DS}$ | Tsi | 2 | — | ns | 1 |
| Data in hold time | $t_{DH}$ | Thi | 1 | — | ns | 1 |
| Address setup time | $t_{AS}$ | Tsi | 2 | — | ns | 1 |
| Address hold time | $t_{AH}$ | Thi | 1 | — | ns | 1 |
| CKE setup time | $t_{CES}$ | Tsi | 2 | — | ns | 1, 5 |
| CKE setup time for power down exit | $t_{CESP}$ | Tpde | 2 | — | ns | 1 |
| CKE hold time | $t_{CEH}$ | Thi | 1 | — | ns | 1 |
| Command setup time | $t_{CS}$ | Tsi | 2 | — | ns | 1 |
| Command hold time | $t_{CH}$ | Thi | 1 | — | ns | 1 |
| Ref/Active to Ref/Active command period | $t_{RC}$ | Trc | 70 | — | ns | 1 |
| Active to precharge command period | $t_{RAS}$ | Tras | 50 | 120000 | ns | 1 |
| Active command to column command (same bank) | $t_{RCD}$ | Trcd | 20 | — | ns | 1 |
| Precharge to active command period | $t_{RP}$ | Trp | 20 | — | ns | 1 |
| Write recovery or data-in to precharge lead time | $t_{DPL}$ | Tdpl | 20 | — | ns | 1 |
| Active (a) to Active (b) command period | $t_{RRD}$ | Trrd | 20 | — | ns | 1 |
| Transition time (rise and fall) | $t_T$ | | 1 | 5 | ns | |
| Refresh period | $t_{REF}$ | | — | 64 | ms | |

Notes: 1. AC measurement assumes $t_T$ = 1 ns. Reference level for timing of input signals is 1.5 V.
2. Access time is measured at 1.5 V. Load condition is $C_L$ = 50 pF.
3. $t_{LZ}$ (min) defines the time at which the outputs achieves the low impedance state.
4. $t_{HZ}$ (max) defines the time at which the outputs achieves the high impedance state.
5. $t_{CES}$ defines CKE setup time to CK rising edge except power down exit command.

**Test Conditions**

- Input and output timing reference levels: 1.5 V
- Input waveform and output load: See following figures



**Relationship Between Frequency and Minimum Latency**

| Parameter | | | HB52E648EN/649EN -A6B/B6B | |
|---|---|---|---|---|
| **Frequency (MHz)** | | | **100** | |
| **$t_{CK}$ (ns)** | **HITACHI Symbol** | **PC100 Symbol** | **10** | **Notes** |
| Active command to column command (same bank) | $I_{RCD}$ | | 2 | 1 |
| Active command to active command (same bank) | $I_{RC}$ | | 7 | = [$I_{RAS}$ + $I_{RP}$] 1 |
| Active command to precharge command (same bank) | $I_{RAS}$ | | 5 | 1 |
| Precharge command to active command (same bank) | $I_{RP}$ | | 2 | 1 |
| Write recovery or data-in to precharge command (same bank) | $I_{DPL}$ | Tdpl | 2 | 1 |
| Active command to active command (different bank) | $I_{RRD}$ | | 2 | 1 |
| Self refresh exit time | $I_{SREX}$ | Tsrx | 1 | 2 |
| Last data in to active command (Auto precharge, same bank) | $I_{APW}$ | Tdal | 4 | = [$I_{DPL}$ + $I_{RP}$] |
| Self refresh exit to command input | $I_{SEC}$ | | 7 | = [$I_{RC}$] 3 |
| Precharge command to high impedance ($\overline{CE}$ latency = 2) | $I_{HZP}$ | Troh | 2 | |
| ($\overline{CE}$ latency = 3) | $I_{HZP}$ | Troh | 3 | |
| Last data out to active command (auto precharge) (same bank) | $I_{APR}$ | | 1 | |
| Last data out to precharge (early precharge) ($\overline{CE}$ latency = 2) | $I_{EP}$ | | –1 | |
| ($\overline{CE}$ latency = 3) | $I_{EP}$ | | –2 | |
| Column command to column command | $I_{CCD}$ | Tccd | 1 | |
| Write command to data in latency | $I_{WCD}$ | Tdwd | 0 | |
| DQMB to data in | $I_{DID}$ | Tdqm | 0 | |
| DQMB to data out | $I_{DOD}$ | Tdqz | 2 | |
| CKE to CK disable | $I_{CLE}$ | Tcke | 1 | |
| Register set to active command | $I_{RSA}$ | Tmrd | 1 | |
| $\overline{S}$ to command disable | $I_{CDD}$ | | 0 | |
| Power down exit to command input | $I_{PEC}$ | | 1 | |

Notes: 1. $I_{RCD}$ to $I_{RRD}$ are recommended value.
2. Be valid [DSEL] or [NOP] at next command of self refresh exit.
3. Except [DSEL] and [NOP]

## Pin Functions

**CK0 to CK3 (input pin):** CK is the master clock input to this pin. The other input signals are referred at CK rising edge.

**$\overline{S0}$ to $\overline{S3}$ (input pin):** When $\overline{S}$ is Low, the command input cycle becomes valid. When $\overline{S}$ is High, all inputs are ignored. However, internal operations (bank active, burst operations, etc.) are held.

**$\overline{RE}$, $\overline{CE}$ and $\overline{W}$ (input pins):** Although these pin names are the same as those of conventional DRAMs, they function in a different way. These pins define operation commands (read, write, etc.) depending on the combination of their voltage levels. For details, refer to the command operation section.

**A0 to A12 (input pins):** Row address (AX0 to AX12) is determined by A0 to A12 level at the bank active command cycle CK rising edge. Column address (AY0 to AY9) is determined by A0 to A9 level at the read or write command cycle CK rising edge. And this column address becomes burst access start address. A10 defines the precharge mode. When A10 = High at the precharge command cycle, all banks are precharged. But when A10 = Low at the precharge command cycle, only the bank that is selected by BA0/BA1 (BS) is precharged.

**BA0/BA1 (input pin):** BA0/BA1 are bank select signal (BS). The memory array is divided into bank 0, bank 1, bank 2 and bank 3. If BA1 is Low and BA0 is Low, bank 0 is selected. If BA1 is High and BA0 is Low, bank 1 is selected. If BA1 is Low and BA0 is High, bank 2 is selected. If BA1 is High and BA0 is High, bank 3 is selected.

**CKE0, CKE1 (input pin):** This pin determines whether or not the next CK is valid. If CKE is High, the next CK rising edge is valid. If CKE is Low, the next CK rising edge is invalid. This pin is used for power-down and clock suspend modes.

**DQMB0 to DQMB7 (input pins):** Read operation: If DQMB is High, the output buffer becomes High-Z. If the DQMB is Low, the output buffer becomes Low-Z.

Write operation: If DQMB is High, the previous data is held (the new data is not written). If DQMB is Low, the data is written.

**DQ0 to DQ63 (input/output pins):** Data is input to and output from these pins.

**CB0 to CB7 (input/output pins):** Data is input to and output from these pins.

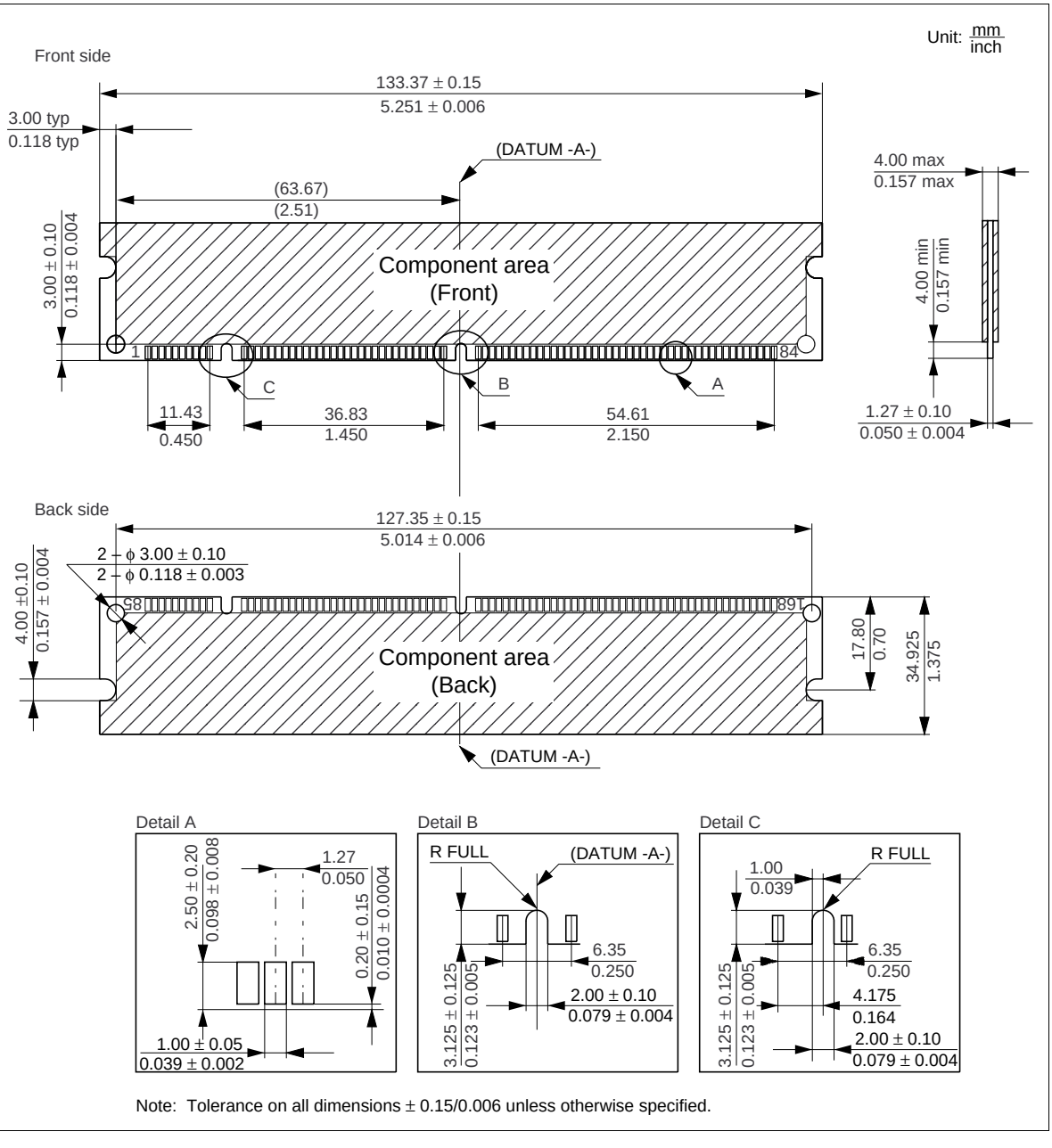
**$V_{CC}$ (power supply pins):** 3.3 V is applied.

**$V_{ss}$ (power supply pins):** Ground is connected.

## Detailed Operation Part

Refer to the HM5225165B/HM5225805B/HM5225405B-75/A6/B6 datasheet.

## Physical Outline




Note: Tolerance on all dimensions ± 0.15/0.006 unless otherwise specified.

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## Revision Record

| Rev. | Date | Contents of Modification | Drawn by | Approved by |
|---|---|---|---|---|
| 0.0 | Oct. 20, 1999 | Initial issue<br>(referred to HM5225165B/HM5225805B/HM5225405B-75/A60/B60 rev 0.0) | T. Kudoh | K. Tsuneda |
| 0.1 | Nov. 29, 1999 | (referred to HM5225165B/HM5225805B/HM5225405B-75/A60/B60 rev 0.0)<br>Deletion of HB52E328EM-A6B/B6B and HB52E329EM-A6B/B6B. | | |